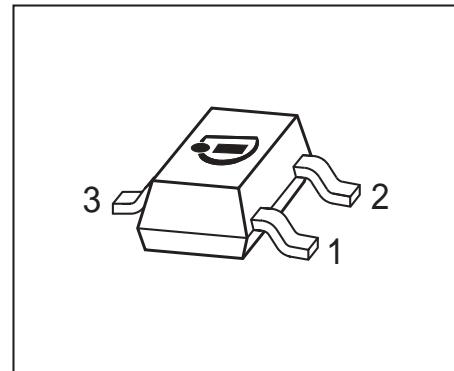


## NPN Silicon AF Transistors

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 Hz and 15 kHz
- Complementary types: BCW61, BCX71 (PNP)
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101



Type	Marking	Pin Configuration			Package
BCW60B	ABs	1=B	2=E	3=C	SOT23
BCW60C	ACs	1=B	2=E	3=C	SOT23
BCW60D	ADs	1=B	2=E	3=C	SOT23
BCW60FF	AFs	1=B	2=E	3=C	SOT23
BCX70G	AGs	1=B	2=E	3=C	SOT23
BCX70H	AHs	1=B	2=E	3=C	SOT23
BCX70J	AJs	1=B	2=E	3=C	SOT23
BCX70K	AKs	1=B	2=E	3=C	SOT23

<sup>1</sup>Pb-containing package may be available upon special request

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage BCW60, ...60FF	$V_{CEO}$	32	V
BCX70		45	
Collector-base voltage BCW60, ...60FF	$V_{CBO}$	32	
BCX70		45	
Emitter-base voltage	$V_{EBO}$	6	
Collector current	$I_C$	100	mA
Peak collector current	$I_{CM}$	200	
Peak base current	$I_{BM}$	200	
Total power dissipation $T_S \leq 71 \text{ }^\circ\text{C}$	$P_{tot}$	330	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$	$\leq 240$	K/W

<sup>1</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 10 \text{ mA}, I_B = 0$ , BCW60, ...60FF $I_C = 10 \text{ mA}, I_B = 0$ , BCX70	$V_{(\text{BR})\text{CEO}}$	32 45	- -	- -	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$ , BCW60, ...60FF $I_C = 10 \mu\text{A}, I_E = 0$ , BCX70	$V_{(\text{BR})\text{CBO}}$	32 45	- -	- -	
Emitter-base breakdown voltage $I_E = 1 \mu\text{A}, I_C = 0$	$V_{(\text{BR})\text{EBO}}$	6	-	-	
Collector-base cutoff current $V_{CB} = 32 \text{ V}, I_E = 0$ , BCW60, ...60FF $V_{CB} = 45 \text{ V}, I_E = 0$ , BCX70 $V_{CB} = 32 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$ , BCW60, ...60FF $V_{CB} = 45 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$ , BCX70	$I_{\text{CBO}}$	- - - -	- - - -	0.02 0.02 20 20	$\mu\text{A}$
Emitter-base cutoff current $V_{EB} = 4 \text{ V}, I_C = 0$	$I_{\text{EBO}}$	-	-	20	nA
DC current gain- $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}, h_{FE}\text{-grp. G}$ $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}, h_{FE}\text{-grp. B/H}$ $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}, h_{FE}\text{-grp. C/J/FF}$ $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}, h_{FE}\text{-grp. D/K}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, h_{FE}\text{-grp. G}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, h_{FE}\text{-grp. B/H}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, h_{FE}\text{-grp. C/J/FF}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, h_{FE}\text{-grp. D/K}$ $I_C = 50 \text{ mA}, V_{CE} = 1 \text{ V}, h_{FE}\text{-grp. G}$ $I_C = 50 \text{ mA}, V_{CE} = 1 \text{ V}, h_{FE}\text{-grp. B/H}$ $I_C = 50 \text{ mA}, V_{CE} = 1 \text{ V}, h_{FE}\text{-grp. C/J/FF}$ $I_C = 50 \text{ mA}, V_{CE} = 1 \text{ V}, h_{FE}\text{-grp. D/K}$	$h_{FE}$	20 20 40 100 120 180 <b>250</b> 380 50 <b>70</b> 90 100	140 200 300 460 170 250 350 500 - - - - - -	- - - - 220 <b>310</b> 460 630 - - - -	-

**DC Electrical Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 10 \text{ mA}, I_B = 0.25 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 1.25 \text{ mA}$	$V_{CEsat}$	-	0.12 0.2	0.25 0.55	V
Base emitter saturation voltage <sup>1)</sup> $I_C = 10 \text{ mA}, I_B = 0.25 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 1.25 \text{ mA}$	$V_{BEsat}$	-	0.7 0.83	0.85 1.05	
Base-emitter voltage <sup>1)</sup> $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 1 \text{ V}$	$V_{BE(ON)}$	- 0.58 -	0.52 0.65 0.78	- 0.7	

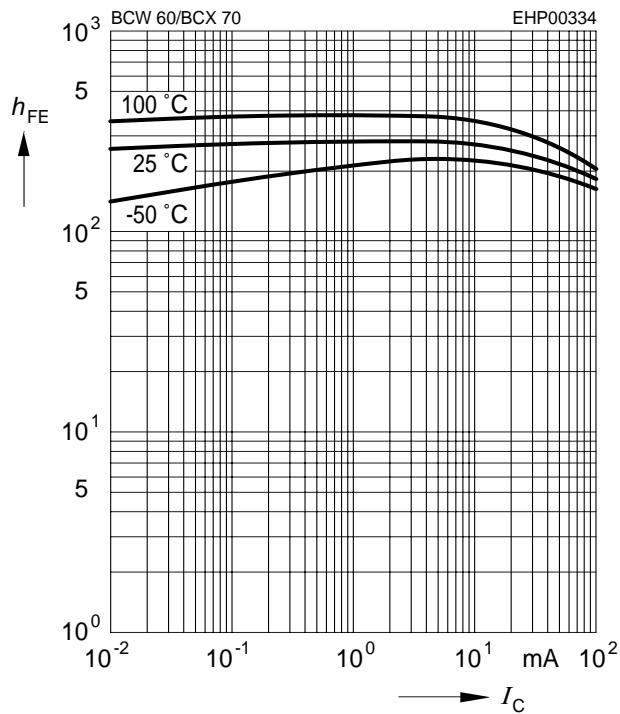
<sup>1)</sup>Pulse test: t < 300μs; D < 2%

**AC Characteristics**

Transition frequency $I_C = 20 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	0.95	-	pF
Emitter-base capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$	$C_{eb}$	-	9	-	
Short-circuit input impedance $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. G}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. B/H}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. C/J/FF}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. D/K}$	$h_{11e}$	-	2.7 3.6 4.5 7.5	-	kΩ
Open-circuit reverse voltage transf. ratio $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. G}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. B/H}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. C/J/FF}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. D/K}$	$h_{12e}$	-	1.5 2 2 3	-	$10^{-4}$
Short-circuit forward current transf. ratio $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. G}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. B/H}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. C/J/FF}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. D/K}$	$h_{21e}$	-	200 260 330 520	-	-
Open-circuit output admittance $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. G}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. B/H}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. C/J/FF}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}, h_{FE}-\text{grp. D/K}$	$h_{22e}$	-	18 24 30 50	-	μS
Noise figure $I_C = 200 \mu\text{A}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz},$ $Df = 200 \text{ Hz}, R_S = 2 \text{ k}\Omega, h_{FE}-\text{grp. B-K}$ $I_C = 200 \mu\text{A}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz},$ $\Delta f = 200 \text{ Hz}, R_S = 2 \text{ k}\Omega, h_{FE}-\text{grp. FF}$	$F$	-	2 1	2	dB
Equivalent noise voltage $I_C = 200 \mu\text{A}, V_{CE} = 5 \text{ V}, R_S = 2 \text{ k}\Omega,$ $f = 10...50 \text{ Hz}, h_{FE}-\text{grp. FF}$	$V_n$	-	-	0.135	μV

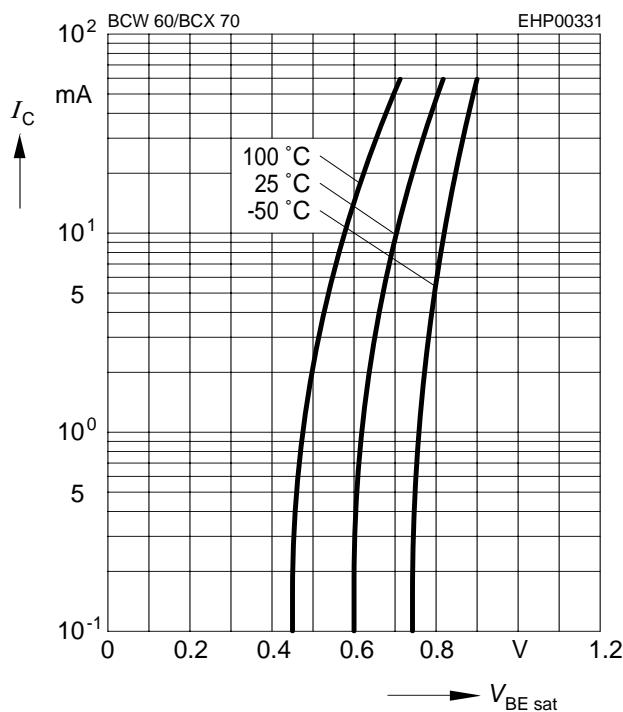
**DC current gain**  $h_{FE} = f(I_C)$

$V_{CE} = 5 \text{ V}$



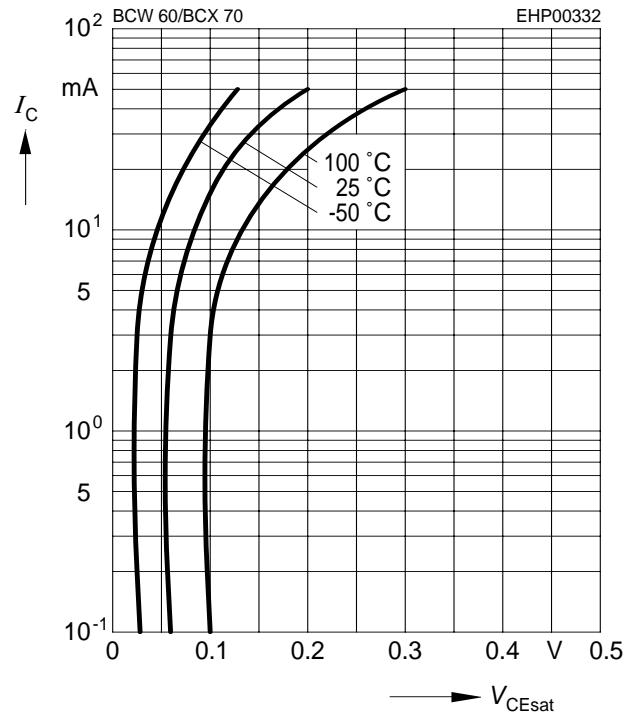
**Base-emitter saturation voltage**

$I_C = f(V_{BEsat})$ ,  $h_{FE} = 40$



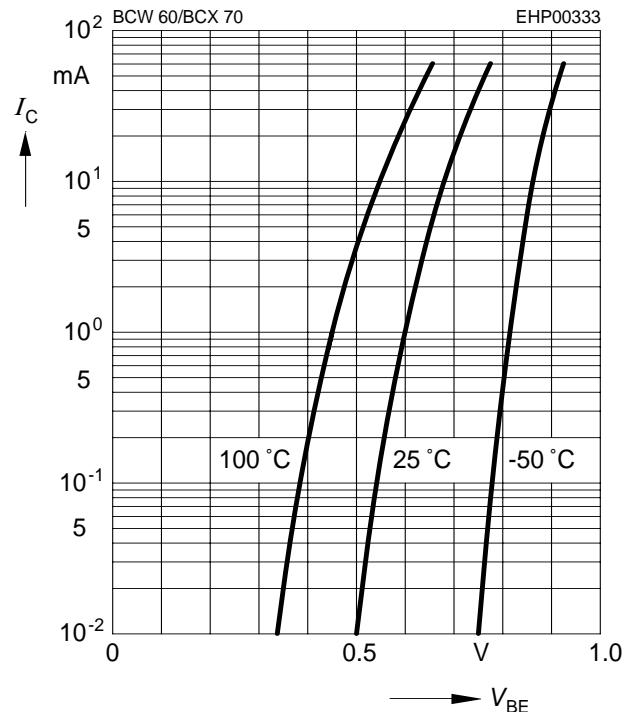
**Collector-emitter saturation voltage**

$I_C = f(V_{CEsat})$ ,  $h_{FE} = 10$

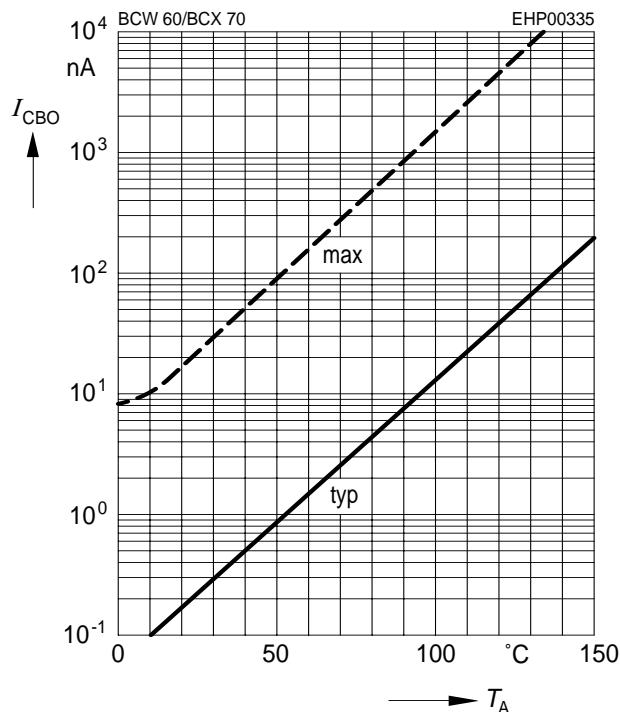


**Collector current**  $I_C = f(V_{BE})$

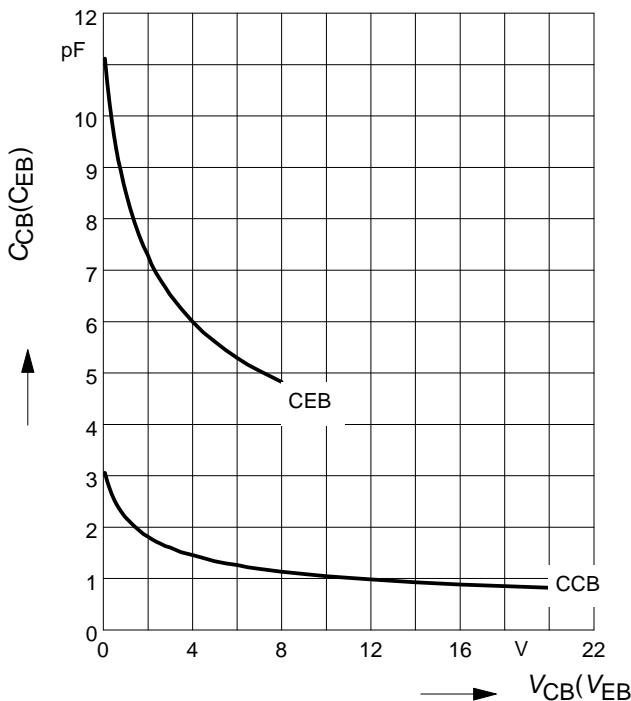
$V_{CE} = 5 \text{ V}$



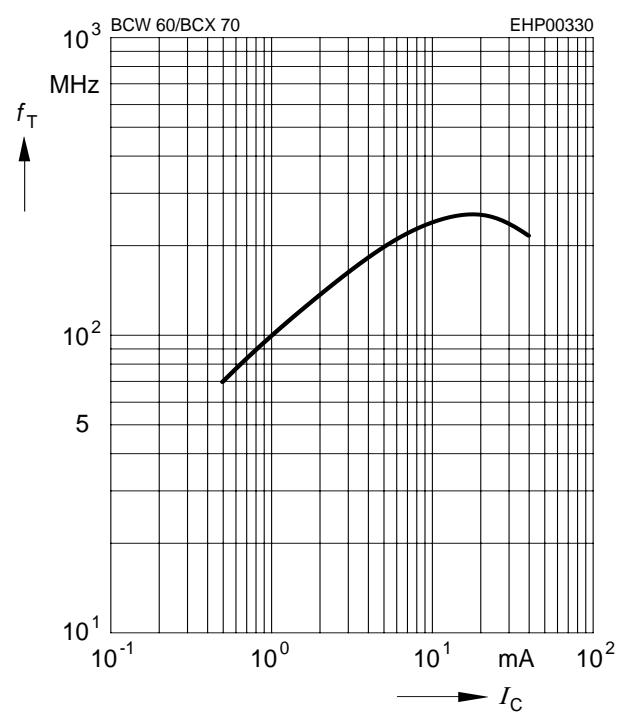
**Collector cutoff current**  $I_{CBO} = f(T_A)$   
 $V_{CB} = V_{CEmax}$



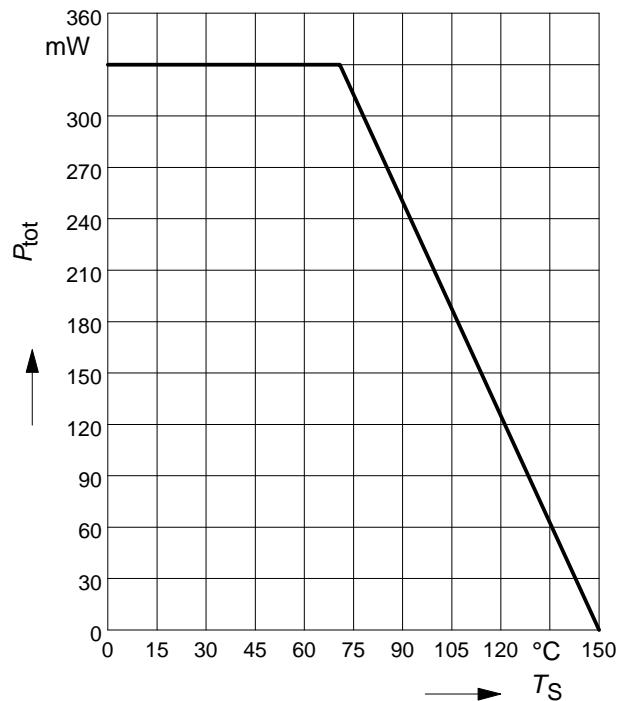
**Collector-base capacitance**  $C_{cb} = f(V_{CB})$   
**Emitter-base capacitance**  $C_{eb} = f(V_{EB})$



**Transition frequency**  $f_T = f(I_C)$   
 $V_{CE} = \text{parameter in } V, f = 2 \text{ GHz}$

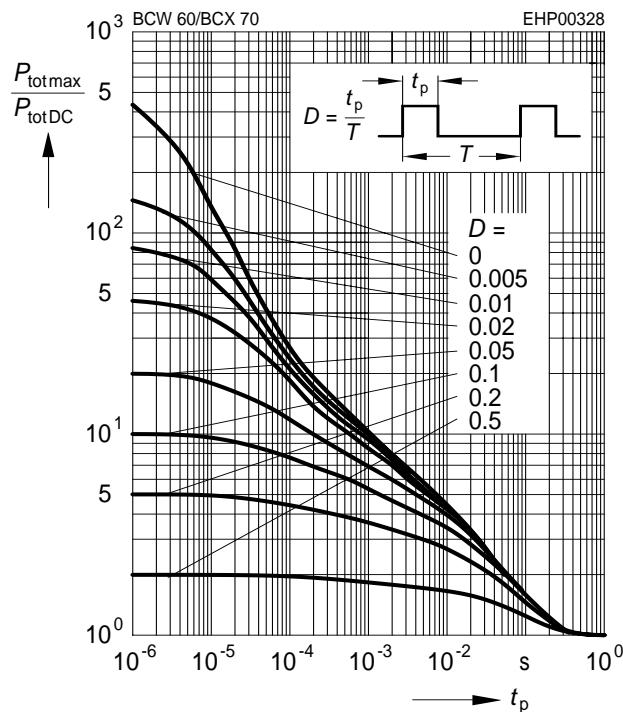


**Total power dissipation**  $P_{tot} = f(T_S)$

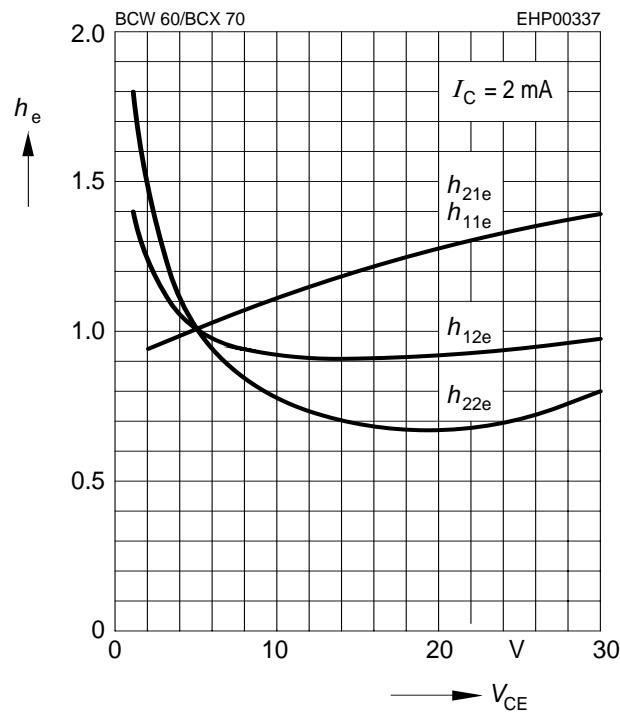


**Permissible Pulse Load**

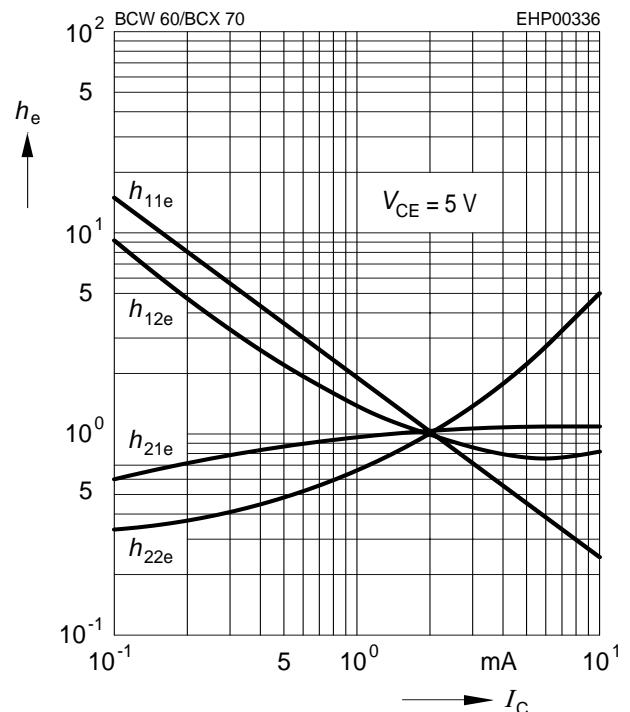
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$



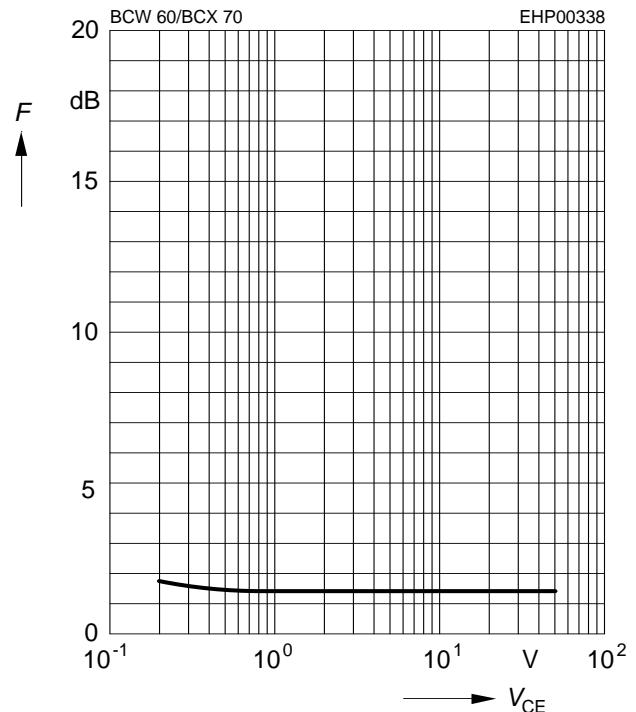
**h parameter  $h_e = f(V_{CE})$  normalized**  
 $I_C = 2\text{mA}$


**h parameter  $h_e = f(I_C)$  normalized**

$$V_{CE} = 5\text{V}$$

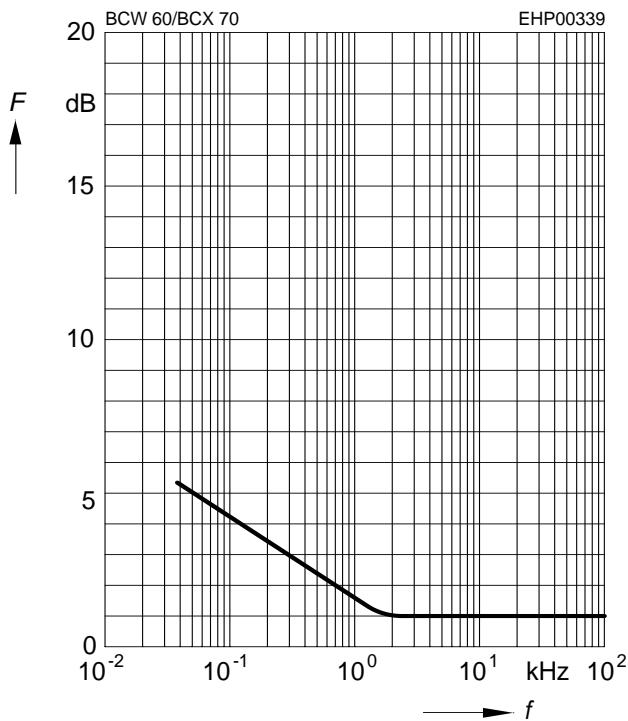

**Noise figure  $F = f(V_{CE})$** 

$$I_C = 0.2\text{mA}, R_S = 2\text{k}\Omega, f = 1\text{kHz}$$



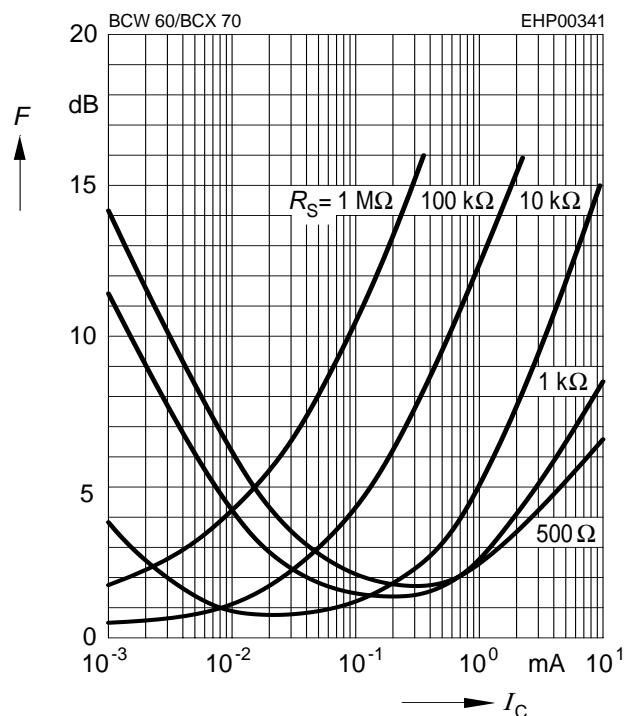
**Noise figure  $F = f(f)$**

$V_{CE} = 5V, Z_S = Z_{Sopt}$



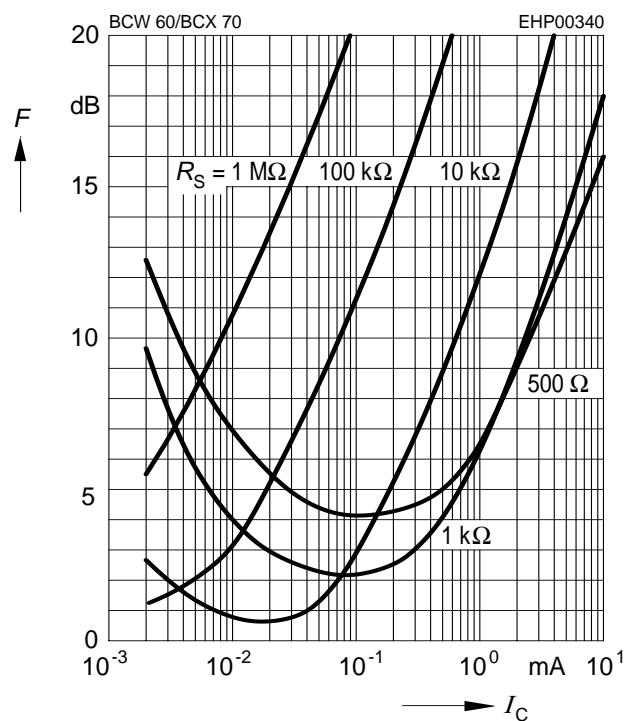
**Noise figure  $F = f(I_C)$**

$V_{CE} = 5V, f = 1\text{kHz}$



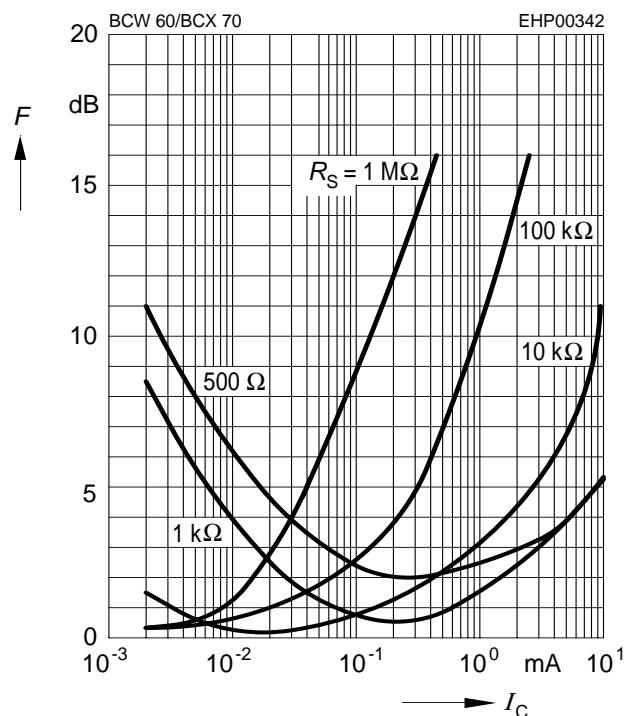
**Noise figure  $F = f(I_C)$**

$V_{CE} = 5V, f = 120\text{Hz}$

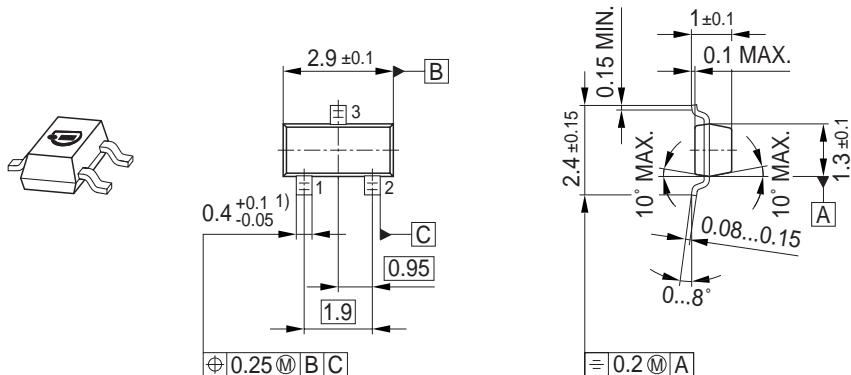


**Noise figure  $F = f(I_C)$**

$V_{CE} = 5V, f = 10\text{kHz}$

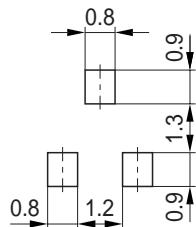


## Package Outline

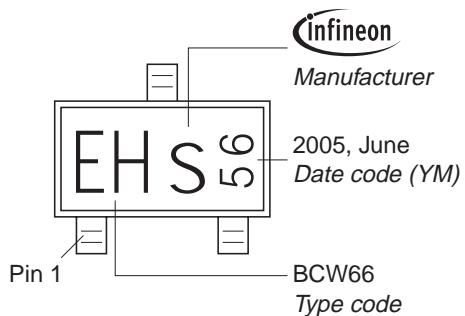


1) Lead width can be 0.6 max. in dambar area

## Foot Print

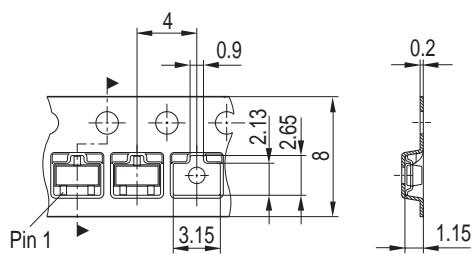


## Marking Layout (Example)



## Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
Reel ø330 mm = 10.000 Pieces/Reel



Edition 2006-02-01

Published by

Infineon Technologies AG

81726 München, Germany

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